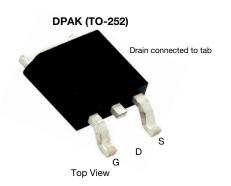
P-Channel 60 V (D-S) MOSFET



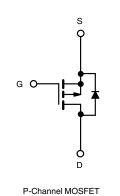
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PRODUCT SUMMARY				
V _{DS} (V)	-60			
$R_{DS(on)}$ max. (Ω) at V_{GS} = -10 V	0.155			
$R_{DS(on)}$ max. (Ω) at V_GS = -4.5 V	0.280			
Q _g typ. (nC)	12.5			
I _D (A)	-8.4			
Configuration	Single			

FEATURES

- TrenchFET[®] power MOSFETs
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>





ORDERING INFORMATION		
Package	DPAK (TO-252)	
Lead (Pb)-free and halogen-free	SUD08P06-155L-GE3	

ABSOLUTE MAXIMUM RATINGS ($T_C = 25 \degree C$, unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Gate-source voltage		V _{GS}	± 20	V
Continuous dusin surrent (T 150 °C)	T _C = 25 °C		-8.2	
Continuous drain current (T _J = 150 °C)	T _C = 100 °C	I _D	-5.2	
Pulsed drain current		I _{DM}	-18	А
Continuing source current (diode conduction)		I _S	-8.4	
Avalanche current		I _{AS}	-12	
Single pulse avalanche energy	L = 0.1 mH	E _{AS}	7.2	mJ
Maximum power dissipation	T _C = 25 °C	D	20.8 ^a	14/
	T _A = 25 °C	P _D	1.7 ^b	W
Operating junction and storage temperature range	·	T _J , T _{stg}	-55 to +150	°C

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT
lunding to each and b	t ≤ 10 s	R _{thJA}	20	25	°C/W
Junction-to-ambient ^b	Steady state		62	75	
Junction-to-case		R _{thJC}	5	6	

Notes

a. See SOA curve for voltage derating

b. Surface mounted on 1" x 1" FR-4 board

SUD08P06-155L-GE3



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PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP. ^a	MAX.	UNIT
Static	•					
Drain-source breakdown voltage	V _{DS}	$V_{GS} = 0 V, I_D = -250 \mu A$	-60	-	-	V
Gate threshold voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \ \mu A$	-1	-2	-	V
Gate-body leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 20 V$	-	-	± 100	nA
		$V_{DS} = -60 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$	-	-	-1	μΑ
Zero gate voltage drain current	I _{DSS}	V_{DS} = -60 V, V_{GS} = 0 V, T_{J} = 125 °C	-	-	-50	
		V_{DS} = -60 V, V_{GS} = 0 V, T_{J} = 150 °C	-	-	-150	
On-state drain current ^b	I _{D(on)}	$V_{DS} = -5 V, V_{GS} = -10 V$	-10	-	-	А
		$V_{GS} = -10 \text{ V}, \text{ I}_{D} = -5 \text{ A}$	-	0.125	0.155	1
Drain-source on-state resistance b	Б	V_{GS} = -10 V, I_{D} = -5 A, T_{J} = 125 °C	-	-	0.280	0
Drain-source on-state resistance 5	R _{DS(on)}	V_{GS} = -10 V, I_D = -5 A, T_J = 150 °C	-	-	0.350	Ω
		$V_{GS} = -4.5 \text{ V}, \text{ I}_{D} = -2 \text{ A}$	-	0.158	0.280	
Forward transconductance b	9 _{fs}	$V_{DS} = -15 \text{ V}, \text{ I}_{D} = -5 \text{ A}$	-	8	-	S
Dynamic	-					
Input capacitance	C _{iss}		-	450	-	pF
Output capacitance	C _{oss}	V_{DS} = -25 V, V_{GS} = 0 V, f = 1 MHz	-	65	-	
Reverse transfer capacitance	C _{rss}		-	40	-	
Total gate charge	Qg		-	12.5	19	
Gate-source charge	Q _{gs}	V_{DS} = -30 V, V_{GS} = -10 V, I_D = -8.4 A	-	2.3	-	nC
Gate-drain charge	Q _{gd}		-	3.2	-	
Gate resistance	R _g	f = 1 MHz	-	8	-	Ω
Turn-on delay time ^c	t _{d(on)}		-	5	10	
Rise time ^c	tr	V_{DD} = -30 V, R_L = 3.57 Ω	-	14	25	
Turn-off delay time ^c	t _{d(off)}	$I_D \cong -8.4$ Å, $V_{GEN} = -10$ V, $R_g = 2.5 \Omega$	-	15	25	ns
Fall time ^c	t _f		-	7	12	
Source-Drain Diode Ratings and Ch	aracteristics (T _C = 25 °C) ^b				
Pulsed current	I _{SM}		-	-	-20	А
Forward voltage ^b	V _{SD}	$I_{F} = -2 \text{ A}, V_{GS} = 0 \text{ V}$	-	-0.9	-1.3	V
Reverse recovery time	t _{rr}		-	50	80	ns
Reverse recovery time	Q _{rr}	I _F = -8 A, di/dt = 100 A/μs	-	80	120	nC

Notes

a. Guaranteed by design, not subject to production testing

b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %

c. Independent of operating temperature

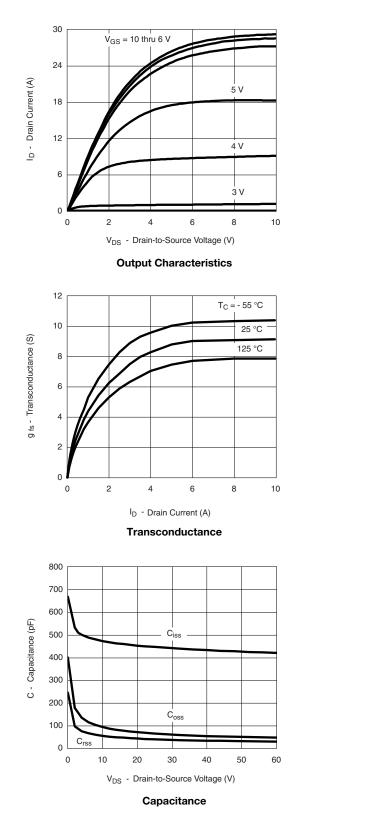
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

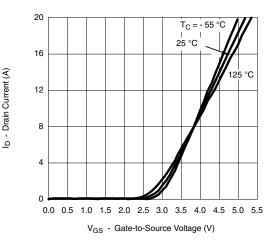


SUD08P06-155L-GE3

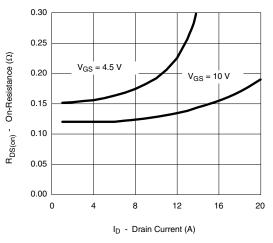
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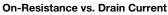
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

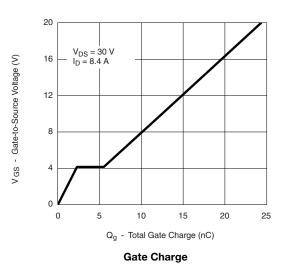




Transfer Characteristics







S13-0788-Rev. A, 15-Apr-13

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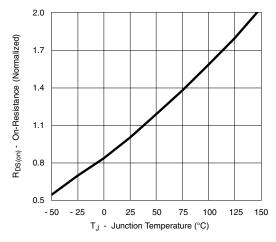
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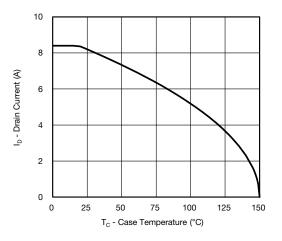
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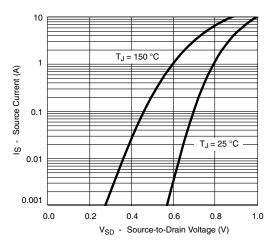
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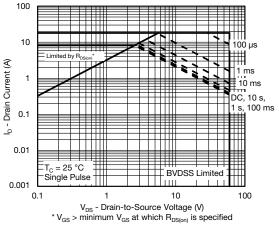
On-Resistance vs. Junction Temperature



Drain Current vs. Case Temperature



Source-Drain Diode Forward Voltage

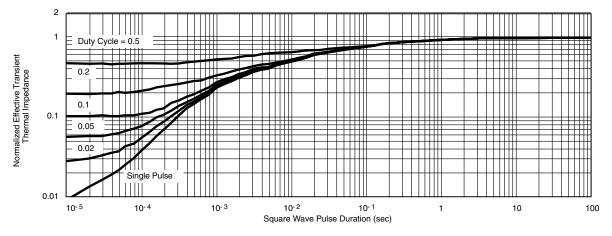


Safe Operating Area

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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?62843.

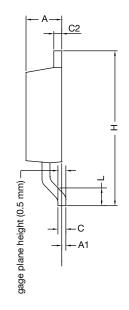


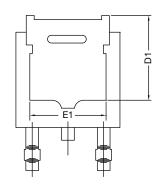


TO-252AA Case Outline

VERSION 1: FACILITY CODE = Y







	MILLIMETERS			
DIM.	MIN.	MAX.		
А	2.18	2.38		
A1	-	0.127		
b	0.64	0.88		
b2	0.76	1.14		
b3	4.95	5.46		
С	0.46	0.61		
C2	0.46	0.89		
D	5.97	6.22		
D1	4.10	-		
E	6.35	6.73		
E1	4.32	-		
Н	9.40	10.41		
е	2.28	BSC		
e1	4.56	4.56 BSC		
L	1.40	1.78		
L3	0.89	1.27		
L4	-	1.02		
L5	1.01	1.52		

Note

• Dimension L3 is for reference only



VERSION 2: FACILITY CODE = N



	MILLIMETERS		
DIM.	MIN.	MAX.	
A	2.18	2.39	
A1	-	0.13	
b	0.65	0.89	
b1	0.64	0.79	
b2	0.76	1.13	
b3	4.95	5.46	
С	0.46	0.61	
c1	0.41	0.56	
c2	0.46	0.60	
D	5.97	6.22	
D1	5.21	-	
E	6.35	6.73	
E1	4.32	-	
е	2.29 BSC		
Н	9.94	10.34	

	MILLIMETERS		
DIM.	MIN.	MAX.	
L	1.50	1.78	
L1	2.74	l ref.	
L2	0.51	BSC	
L3	0.89	1.27	
L4	-	1.02	
L5	1.14	1.49	
L6	0.65	0.85	
θ	0°	10°	
θ1	0°	15°	
θ2	25°	35°	

Notes

• Dimensioning and tolerance confirm to ASME Y14.5M-1994

• All dimensions are in millimeters. Angles are in degrees

• Heat sink side flash is max. 0.8 mm

Radius on terminal is optional

ECN: E22-0399-Rev. R, 03-Oct-2022 DWG: 5347



RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)

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